

CLAIMS

What is claimed is:

1. An intermediate structure of a post-probe tested semiconductor device comprising:
 - at least one opened fuse structure; and
 - a metal feature plated on a first metal structure of said intermediate structure, said metal feature formed after probe testing, wherein said at least one opened fuse structure is not reformed by a metal of said metal feature.
2. The intermediate structure of claim 1, wherein said metal feature comprises an electrolessly plated metal feature.
3. The intermediate structure of claim 1, wherein said metal feature is a metal layer, an interconnect cap, a redistribution layer, or a bond pad.
4. The intermediate structure of claim 3, wherein said metal feature is said metal layer.
5. The intermediate structure of claim 1, wherein said metal feature comprises nickel, palladium, gold, tin, silver, or copper.
6. The intermediate structure of claim 5, wherein said metal feature comprises nickel.
7. The intermediate structure of claim 1, wherein said first metal structure comprises at least one bond pad.
8. The intermediate structure of claim 1, wherein said intermediate structure is an intermediate structure of an SRAM or FLASH memory chip.

9. An intermediate structure of a post-probe tested semiconductor device produced by a method comprising:
- providing said intermediate structure comprising an exposed metal structure and at least one opened fuse;
 - adjusting a concentration of stabilizer in an electroless plating solution; and
 - electrolessly plating a metal feature on said exposed metal structure without depositing a metal of said metal feature on said at least one opened fuse.
10. The intermediate structure of claim 9, wherein said metal feature is a metal layer, an interconnect cap, a redistribution layer, or a bond pad.
11. The intermediate structure of claim 9, wherein said metal feature comprises nickel, palladium, gold, tin, silver, or copper.
12. The intermediate structure of claim 9, wherein said exposed metal structure comprises at least one bond pad.
13. The intermediate structure of claim 9, wherein providing said intermediate structure comprising an exposed metal structure and at least one opened fuse comprises providing an intermediate structure of an SRAM or FLASH memory chip.
14. The intermediate structure of claim 9, wherein adjusting a concentration of stabilizer in an electroless plating solution comprises adjusting a concentration of stabilizer selected from the group consisting of compounds of group VI elements, compounds comprising oxygen, heavy metal cations, and unsaturated organic acids.
15. The intermediate structure of claim 14, wherein said compounds of group VI elements comprise compounds of S, Se, or Te.

16. The intermediate structure of claim 14, wherein said compounds comprising oxygen comprise compounds of AsO_2^- , IO_3^- , or MoO_4^- .

17. The intermediate structure of claim 14, wherein said heavy metal cations comprise Sn, Pb, Hg, or Sb.

18. The intermediate structure of claim 14, wherein said unsaturated organic acids comprise maleic acid or itaconic acid.